杰力科技股份有限公司
Excelliance MOS Corporation

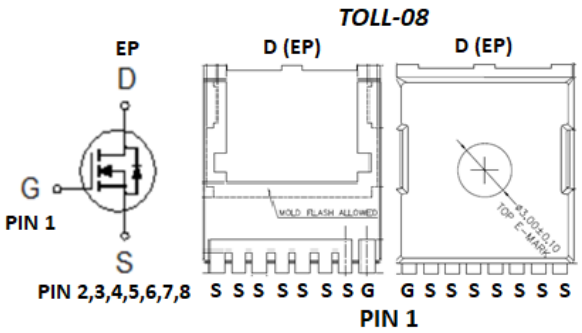
EMD02N10TL8

Single N-Channel Logic Level Enhancement Mode Field Effect Transistor

▪Product Summary:

	N-CH
BV_{DSS}	100V
$R_{DSON\ (Max.)}$@V_{GS}=10V	2mΩ
$R_{DSON\ (Max.)}$@V_{GS}=7V	2.6mΩ
I_D @T_C=25°C	319A
I_D @T_A=25°C	31A

▪ Pin Description:



Single N Channel MOSFET
UIS, Rg 100% Tested
RoHS Compliant & Halogen Free & TSCA Compliant

▪ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	319	A
	T_C = 100 °C		201	
Continuous Drain Current	T_A = 25 °C	I_D	31	
	T_A = 70 °C		24	
Pulsed Drain Current[1]		I_{DM}	791	
Avalanche Current		I_{AS}	88	
Avalanche Energy	L = 0.1mH	EAS	387.2	mJ
Repetitive Avalanche Energy[2]	L = 0.05mH	EAR	193.6	
Power Dissipation	T_C = 25 °C	P_D	313	W
	T_C = 100 °C		125	
Power Dissipation	T_A = 25 °C	P_D	3	W
	T_A = 70 °C		1.9	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

▪ 100% UIS testing in condition of VD=50V, L=0.1mH, VG=10V, IL=53A, Rated VDS=100V N-CH

▪THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		0.4	°C/W
Junction-to-Ambient[3]	$R_{\theta JA}$		42	

[1]Pulse width limited by maximum junction temperature.
[2]Duty cycle < 1%
[3]42°C / W when mounted on a 1 in^2 pad of 2 oz copper.
[4]Guarantee by Engineering test

▪ **ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage[4]	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100			V
Gate Threshold Voltage[4]	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3	4	
Gate-Body Leakage[4]	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current[4]	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	μA
		V_{DS} =70V, V_{GS} =0V, T_J = 125 °C			25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 5V, V_{GS} = 10V	319			A
Drain-Source On-State Resistance[1,4]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 50A		1.5	2	mΩ
		V_{GS} =7V, I_D = 20A		2	2.6	
DYNAMIC						
Input Capacitance[5]	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz		9981		pF
Output Capacitance[5]	C_{oss}			1967		
Reverse Transfer Capacitance[5]	C_{rss}			114		
Gate Resistance[4,5]	R_g	f = 1MHz		1.1		Ω
Total Gate Charge[1,2,5]	Q_g(V_{GS}=10V)	V_{DS} = 50V, V_{GS} = 10V, I_D = 50A		146.5		nC
	Q_g(V_{GS}=7V)			110.9		
Gate-Source Charge[1,2,5]	Q_{gs}			38.7		
Gate-Drain Charge[1,2,5]	Q_{gd}			41		
Turn-On Delay Time[1,2,5]	$t_{d(on)}$	V_{DS} = 50V, V_{GS} = 10V, I_D = 5A , Rg = 3Ω		36.5		nS
Rise Time[1,2,5]	t_r			45.4		
Turn-Off Delay Time[1,2,5]	$t_{d(off)}$			122		
Fall Time[1,2,5]	t_f			122.1		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Continuous Current	I_S				319	A
Pulsed Current[3]	I_{SM}				791	
Forward Voltage[1,4]	V_{SD}	I_F = 50A, V_{GS} = 0V			1.3	V
Reverse Recovery Time[5]	t_{rr}	I_F = 50A, dI_F/dt = 100A / μS		137.1		nS
Peak Reverse Recovery Current[5]	$I_{RM(REC)}$			3.74		A
Reverse Recovery Charge[5]	Q_{rr}			304.6		nC

[1]Pulse test : Pulse Width ≦ 300 usec, Duty Cycle ≦ 2%.

[2]Independent of operating temperature.

[3]Pulse width limited by maximum junction temperature.

[4]Guarantee by FT test Item

[5]Guarantee by Engineering test

EMC will review datasheet by quarter, and update new version.

▪TYPICAL CHARACTERISTICS

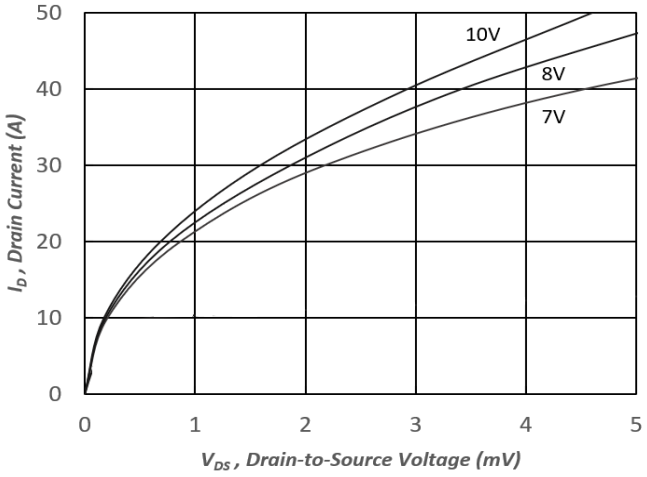


Fig.1 Typical Output Characteristics

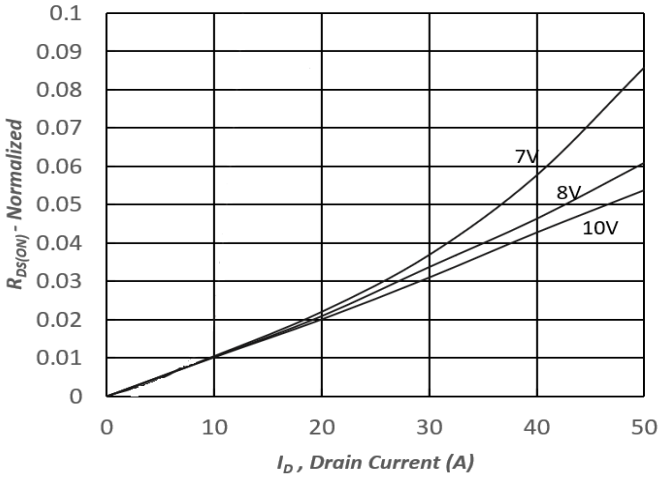


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

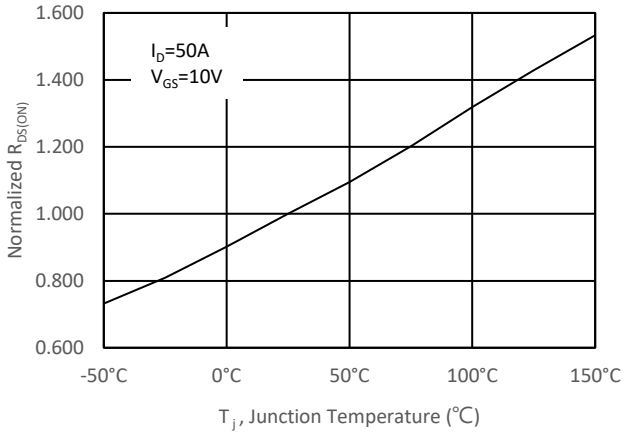


Fig.3 Normalized On-Resistance v.s. Junction Temperature

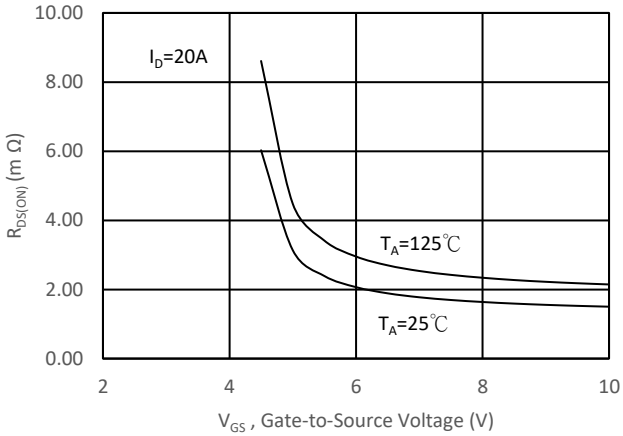


Fig.4 On-Resistance v.s. Gate Voltage

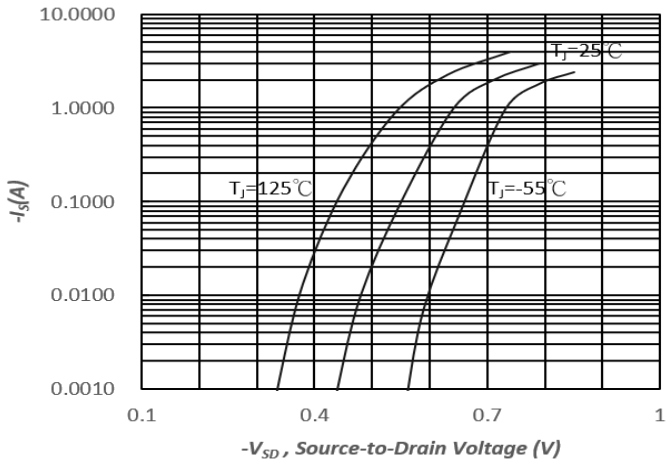


Fig.5 Forward Characteristic of Reverse Diode

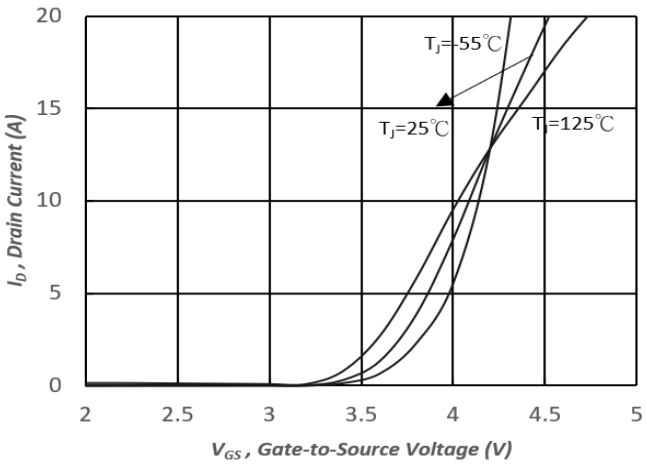


Fig.6 Transfer Characteristics

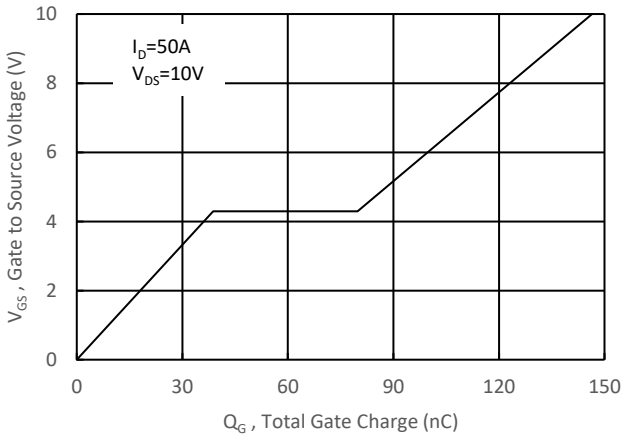


Fig.7 Gate Charge Characteristics

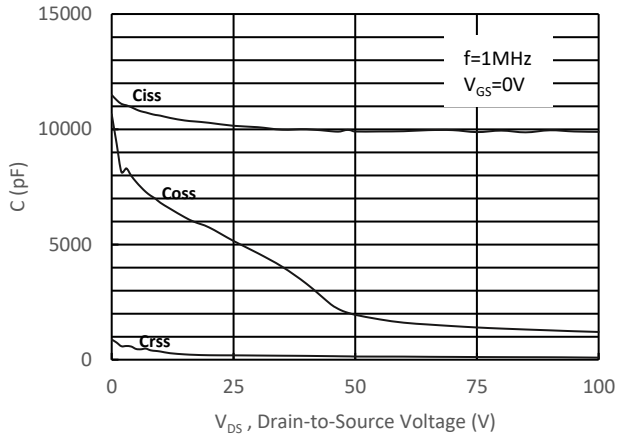


Fig.8 Typical Capacitance Characteristics

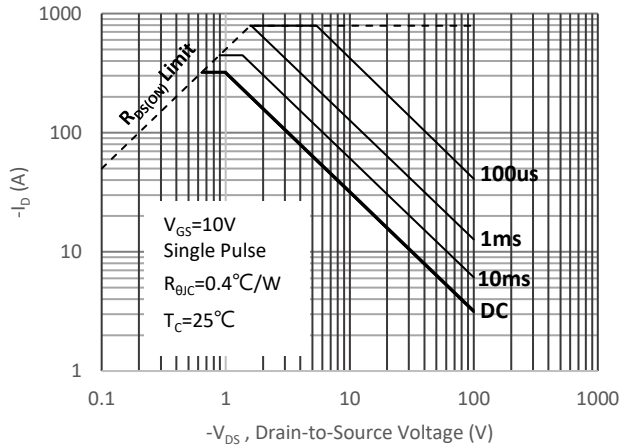


Fig 9. Maximum Safe Operating Area

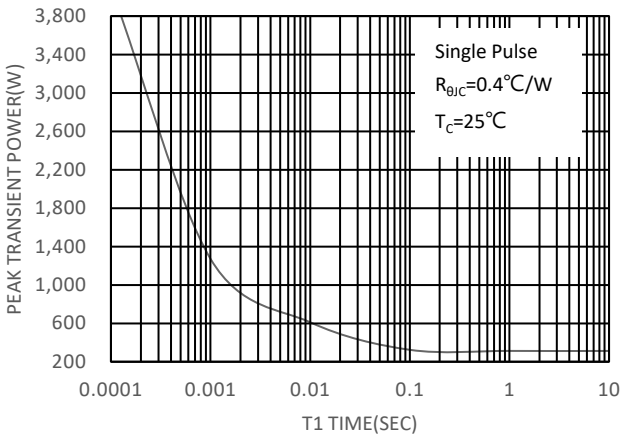


Fig 10. Single Pulse Maximum Power Dissipation

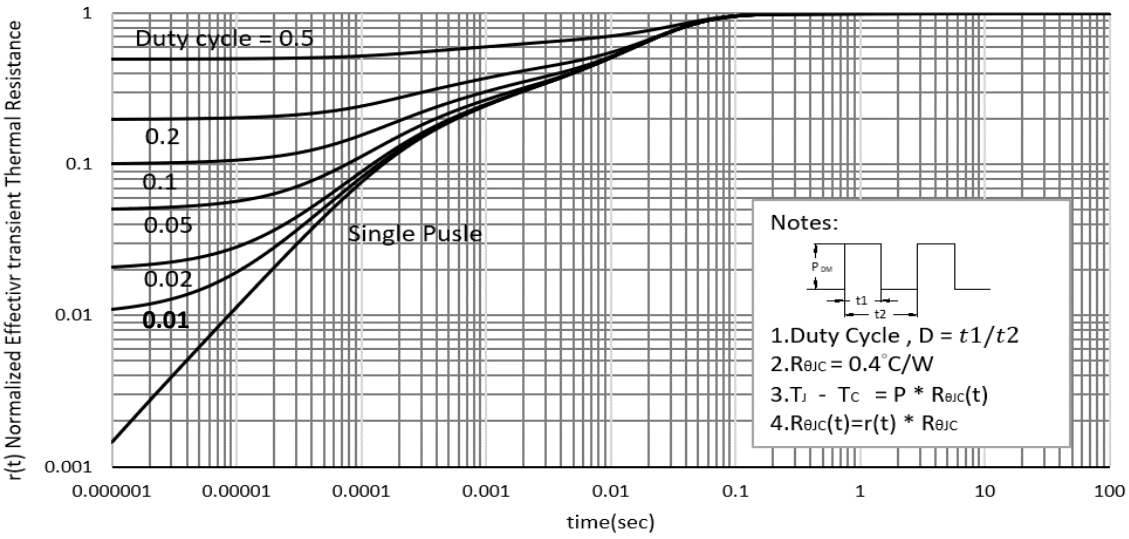
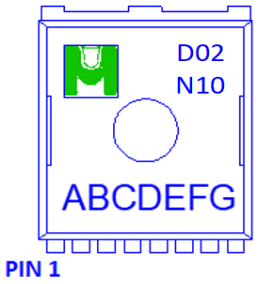


Fig 11. Effective Transient Thermal Impedance

Ordering & Marking Information:

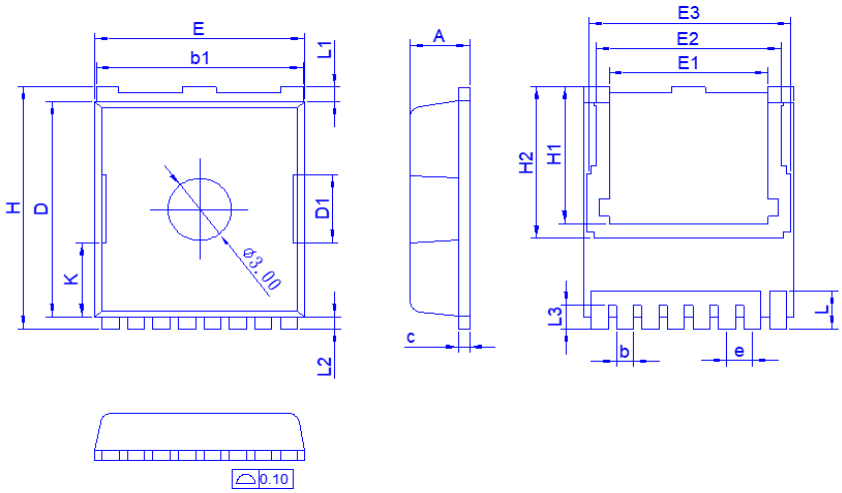
Device Name: EMD02N10TL8 for TOLL-08



D02N10: Device Name

ABCDEFG: Date Code
A: Assembly House
B: Year(A:2008 B:2009 C:2010….)
C: Month(A:01 B:02 C:03 D:04 E:05 F:06 G:07 H:08 I:09 J:10 K:11 L:12)
DEFG: Serial No.

Outline Drawing

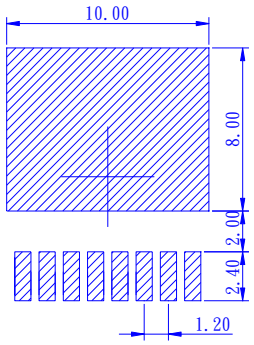


Dimension in mm

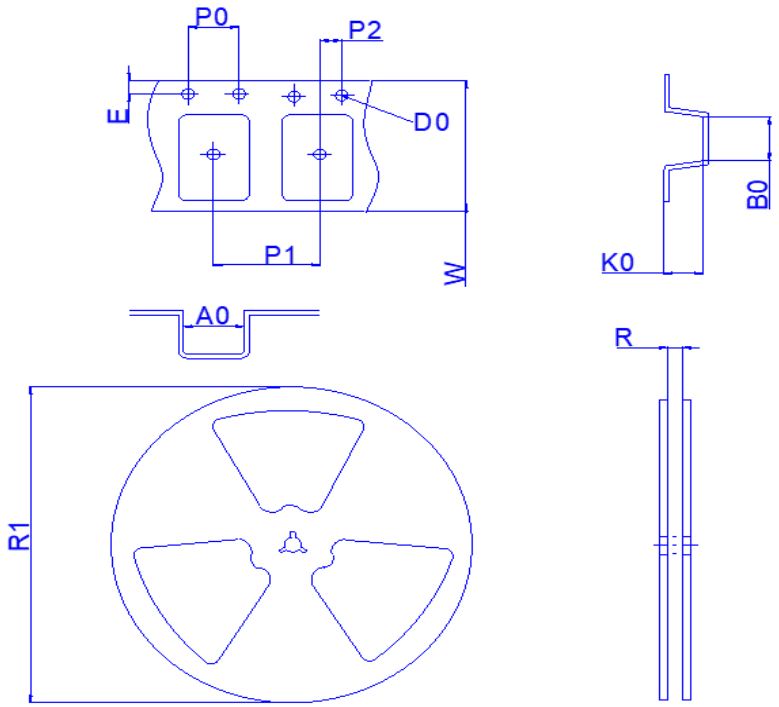
Dimension	A	b	b1	c	D	D1	E	E1	E2	E3	e	H	H1
Min	2.15	0.65	9.70	0.40	10.18	2.85	9.70	7.25	8.00	9.30	1.10	11.48	6.03
Typ.	2.30	0.75	9.80	0.50	10.38	3.00	9.90	7.40	8.10	9.40	1.20	11.68	6.18
Max	2.45	0.90	9.90	0.60	10.58	3.45	10.10	8.40	9.25	9.95	1.30	11.88	7.10

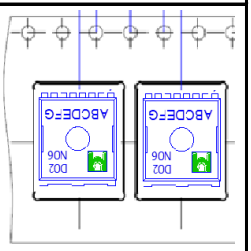
Dimension	H2	K	L	L1	L2	L3
Min	6.85	4.03	1.40	0.50	0.45	1.00
Typ.	7.00	4.18	1.70	0.70	0.60	1.15
Max	7.50	4.55	2.10	0.90	0.75	1.30

Footprint



◆Tape&Reel Information:2000 pcs/Reel(Dimension in millimeter)



產品別	TOLL-08
Reel尺寸	13”
編帶方式	

Dimension in mm

Dimension	Carrier tape									Reel	
	A0	B0	D0	E	K0	P0	P1	P2	W	R	R1
Typ.	10.5	12.28	1.5	1.75	2.7	4	12	2	24	24	330
±	0.2	0.2	0.1	0.1	0.2	0.1	0.2	0.1	0.3	2	2